

2N5114 | 2N5115 | 2N5116 P-CHANNEL JFETS - 2

ELECTRICAL SPECIFICATIONS

Typical @ 25°C unless otherwise noted

Parameter		Symbol	Min.	Max.	Unit
Gate-Source Breakdown Voltage V _{DS} =OVdc, I _G = 1.0µAdc		V _{(BR)GSS}	30		Vdc
Gate-Source "Off" State Voltage V _{DS} = -15Vdc, ID = -1.OnAdc	2N5114 2N5115 2N5116	V _{GS(off)}	5.0 3.0 1.0	10.0 6.0 4.0	Vdc Vdc Vdc
Gate Reverse Current V _{DS} = OVdc, V _{GS} = 20Vdc		I _{ess}		500	pA
Drain Cutoff Current V_{DS} = -15Vdc, V_{GS} = 12Vdc V_{DS} = -15Vdc, V_{GS} = 7Vdc V_{DS} = -15Vdc, V_{GS} = 5Vdc	2N5114 2N5115 2N5116	I _{D(off)}		-500 -500 -500	pA pA pA
Small Signal Drain to Source "On" Resistance V _{GS} = OVdc, I _D = -1mAdc V _{GS} = OVdc, I _D = OAdc, f = 1kHz	2N5114 2N5115 2N5116	R _{DS(on)}		75 100 175	Ω Ω Ω
Drain Source "On" State Voltage V _{GS} = OVdc, I _D = -15mAdc V _{GS} = OVdc, I _D = -7mAdc V _{GS} = OVdc, I _D = -3mAdc	2N5114 2N5115 2N5116	V _{DS(on)}		-1.3 -0.8 -0.6	Vdc Vdc Vdc
Small Signal, Common Source Reverse Transfer Capacitance V _{GS} = 12Vdc, V _{DS} = 0Vdc V _{GS} = 7Vdc, V _{DS} = 0Vdc V _{GS} = 5Vdc, V _{DS} = 0Vdc	2N5114 2N5115 2N5116	\mathbf{C}_{rss}		7	pF
Small Signal, Common Source Short-Circuit Input Capacitance V _{GS} = OVdc V _{DS} = -15Vdc, f = 1.0MHz	2N5114 2N5115 2N5116	C _{iss}		25 25 27	pF
Turn On Delay Time	2N5114 2N5115 2N5116	t _{D(on)}		6 10 25	nS nS nS
Rise Time	2N5114 2N5115 2N5116	t,		10 20 35	nS nS nS
Turn Off Delay Time	2N5114 2N5115 2N5116	t _{d(off)}		6 8 20	nS nS nS

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